

Chapter 5

Elements of Physical Design

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Outline

- Basic Concepts
- Layout of Basic Structures
- Cell Concepts
- MOS Sizing
- Physical Design of Logic Gates
- Design Hierarchies

Basic Concepts

- *Physical design*
 - The actual process of creating circuits on silicon
 - During this phase, schematic diagrams are carefully translated into sets of geometric patterns that are used to define the on-chip physical structures
- Every layer in the CMOS fabrication sequence is defined by a distinct pattern
- The process of physical design is performed using a computer tool called a **layout editor**
 - A graphics program that allows the designer to specify the shape, dimensions, and placement
- Complexity issues are attacked by first designing simple gates and storing their descriptive files in a **library** subdirectory or folder

Basic Concepts

- The gates constitute **cells** in the library
- Library cells are used as building blocks by creating copies of the basic cells to construct a larger more complex circuit
 - This process is called *instantiate* of the cell
 - A copy of a cell is called an *instance*
- Much of the designer's work is directed toward the goal of obtaining a fast circuit in the minimum amount of area
 - Small changes in the shapes or area of a polygon will affect the resulting electrical characteristics of the circuit

CAD Toolsets

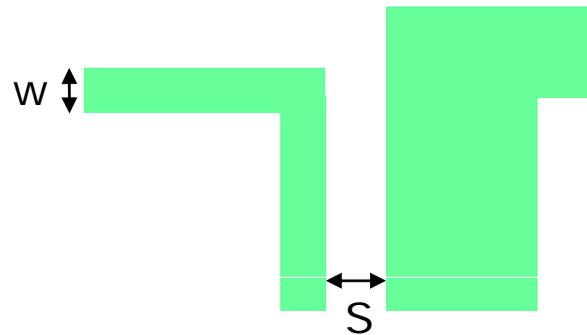
- Physical design is based on the use of CAD tools
 - Simplify the procedure and aid in the verification process
- Physical design toolsets
 - Layout editor
 - Extraction routine
 - Layout versus schematic (LVS)
 - Design rule checker (DRC)
 - Place and route routine
 - Electrical rule checker (ERC)

Layout of Basic Structures

- The masking sequence of the P-substrate technology was established as
 - Start with P-type substrate
 - nWell
 - Active
 - Poly
 - pSelect
 - nSelect
 - Active Contact
 - Poly contact
 - Metal1
 - Via
 - Metal2
 - ...

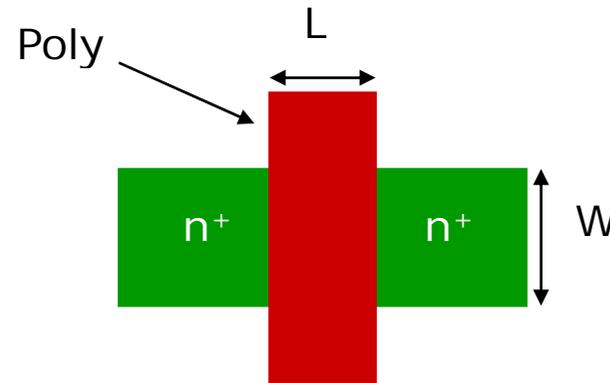
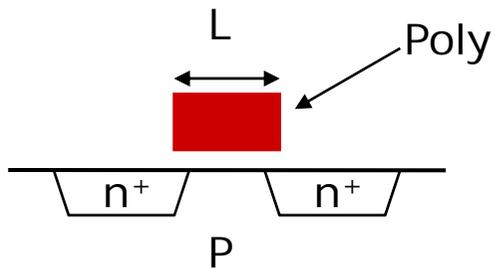
Layout of Basic Structures

- It is worth remembering that the features on every level have design rule specifications for the minimum width w of a line, and a minimum edge-to-edge spacing s between adjacent polygons
 - For example,

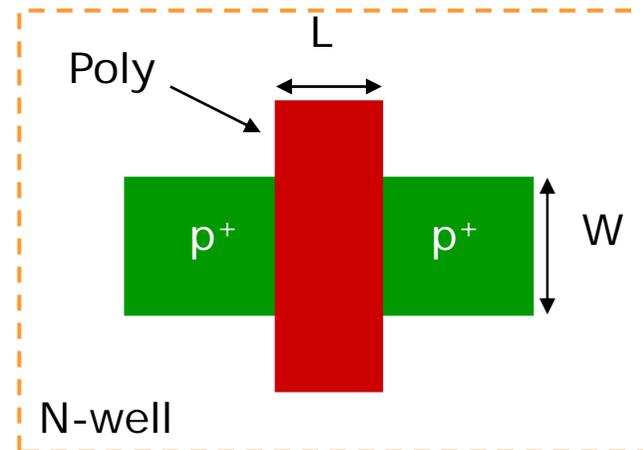
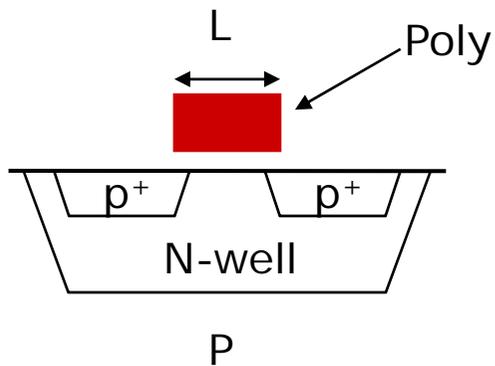


Layouts of PMOS & NMOS

□ NMOS

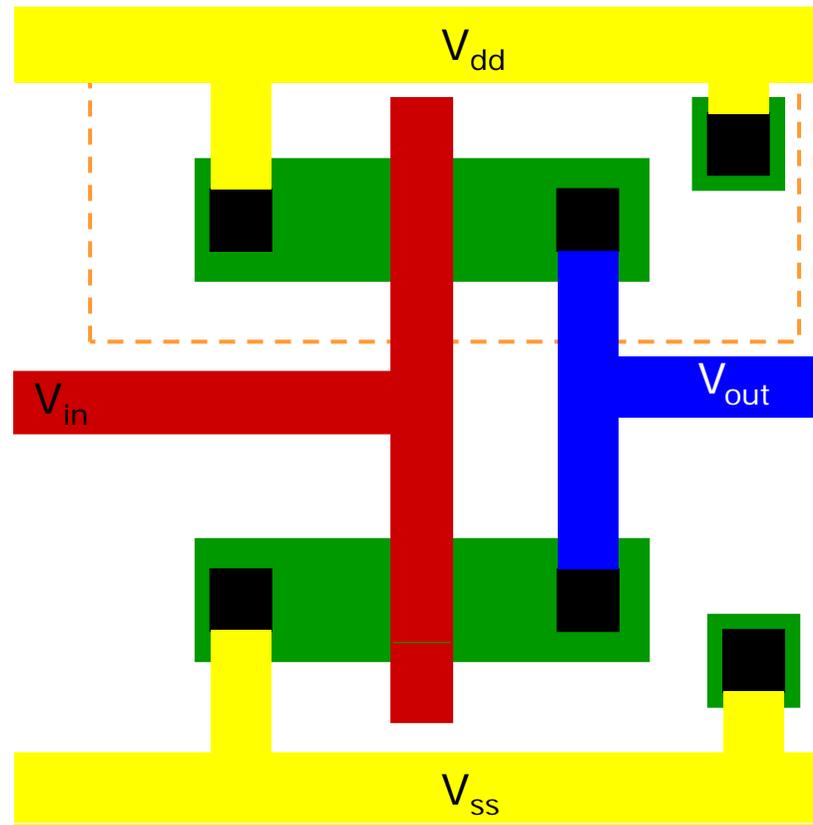
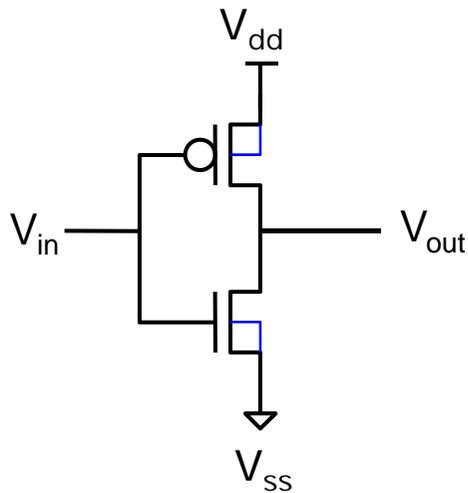


□ PMOS

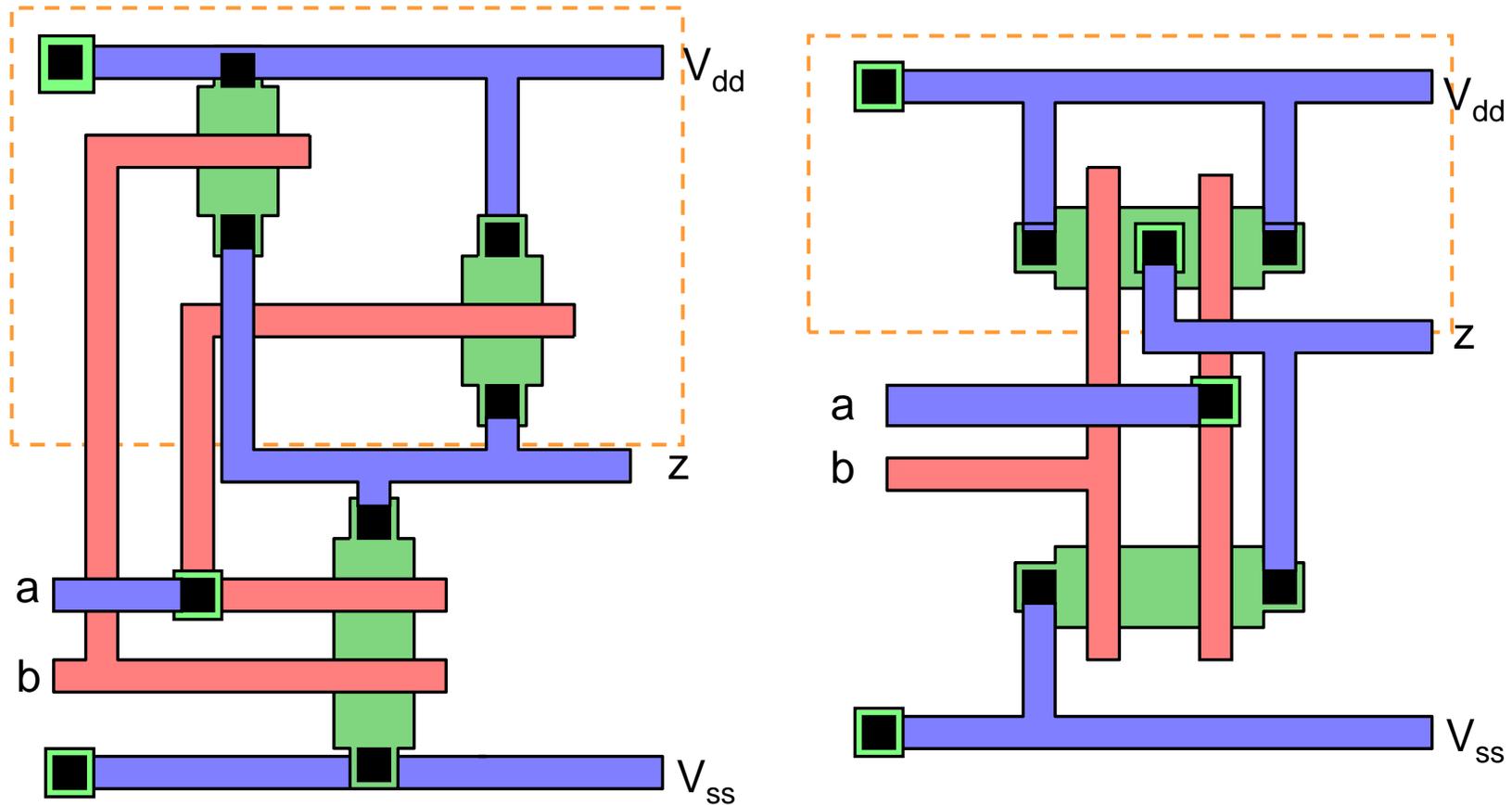


The Layout of a CMOS Inverter

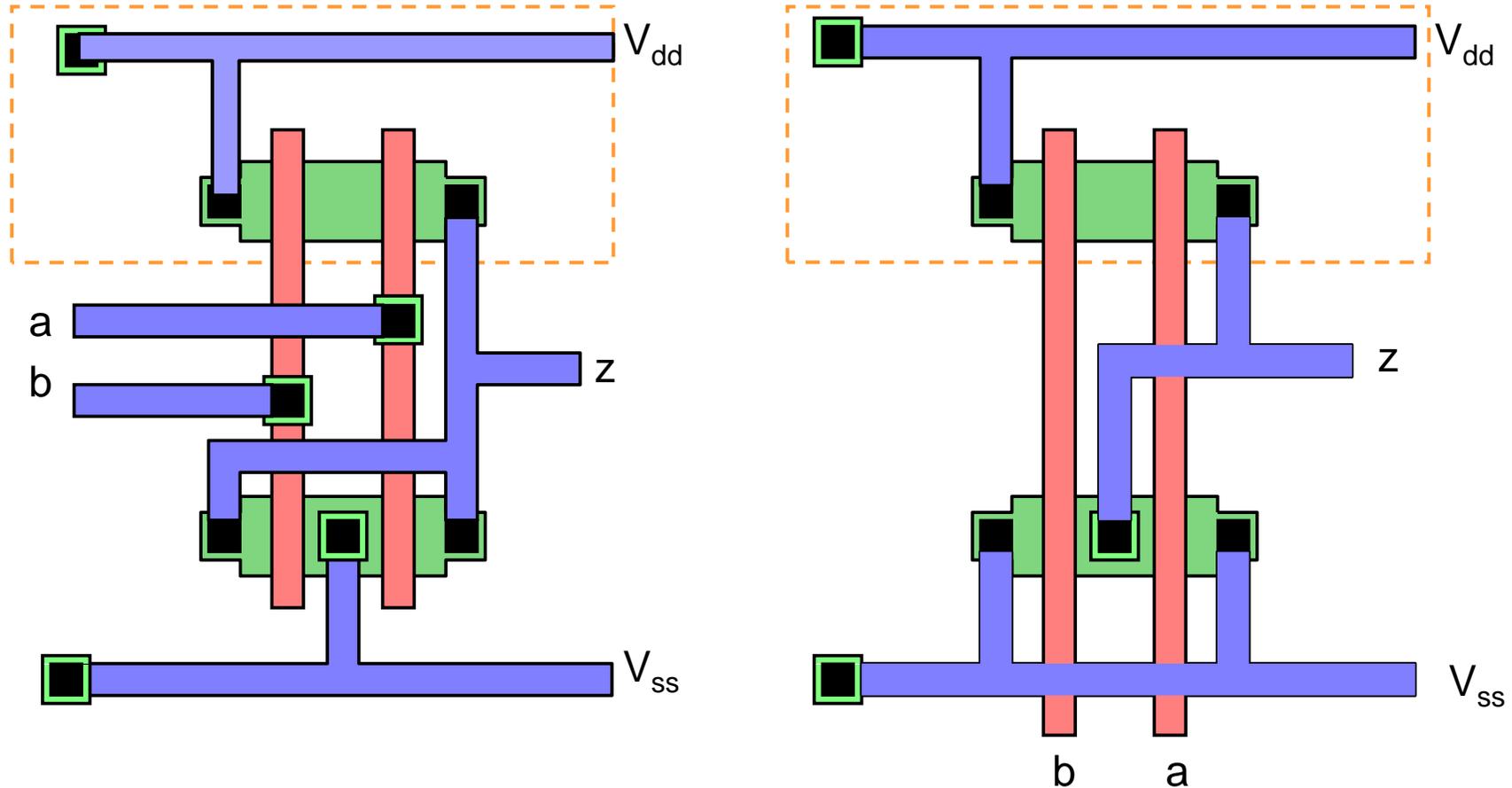
- A transistor-level CMOS inverter & the corresponding layout



Layouts of a 2-Input NAND Gate

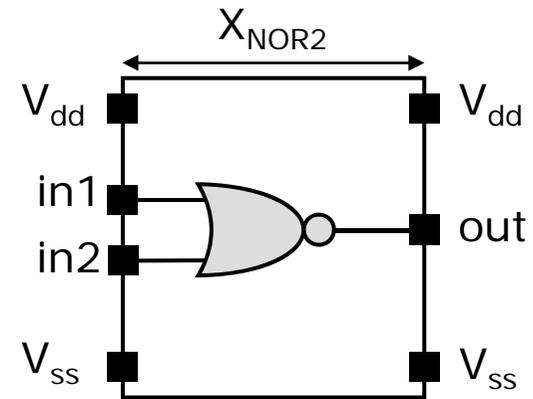
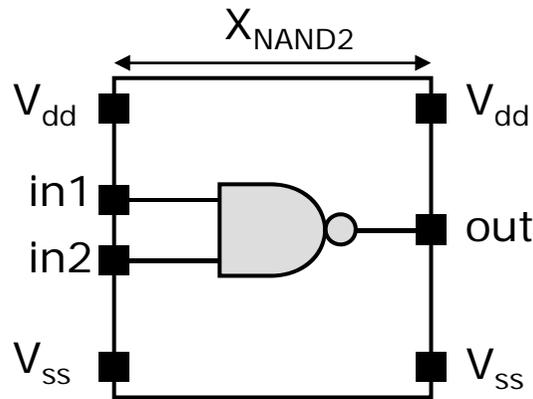
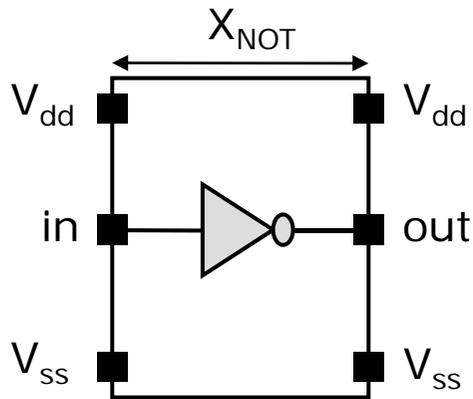


Layouts of a 2-Input NOR Gate



Cell Concepts

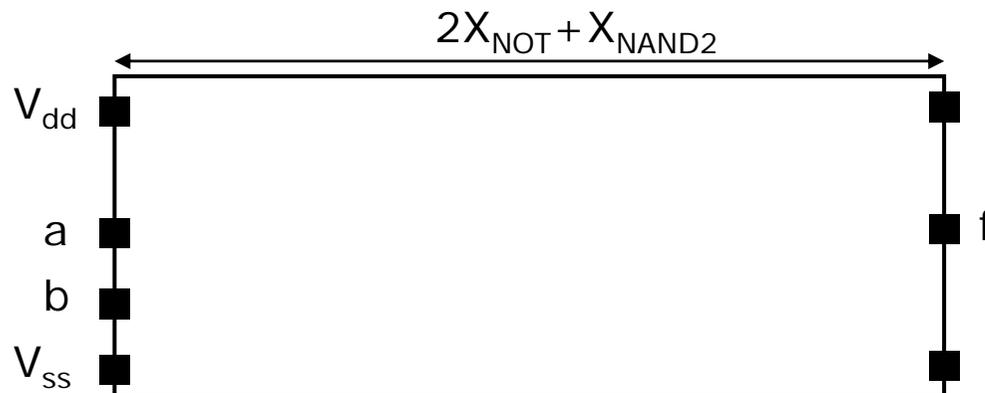
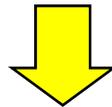
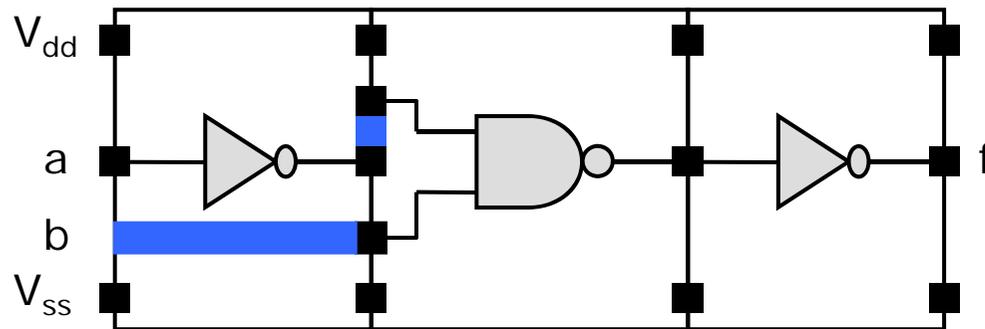
- The basic building blocks in physical design are called **cells**
- Logic gates as basic cells



- Note that power supply ports for V_{dd} and V_{ss} are chosen to be at the same locations for every cell
- The width of each cell depends on the transistor sizes and wiring used at the physical level

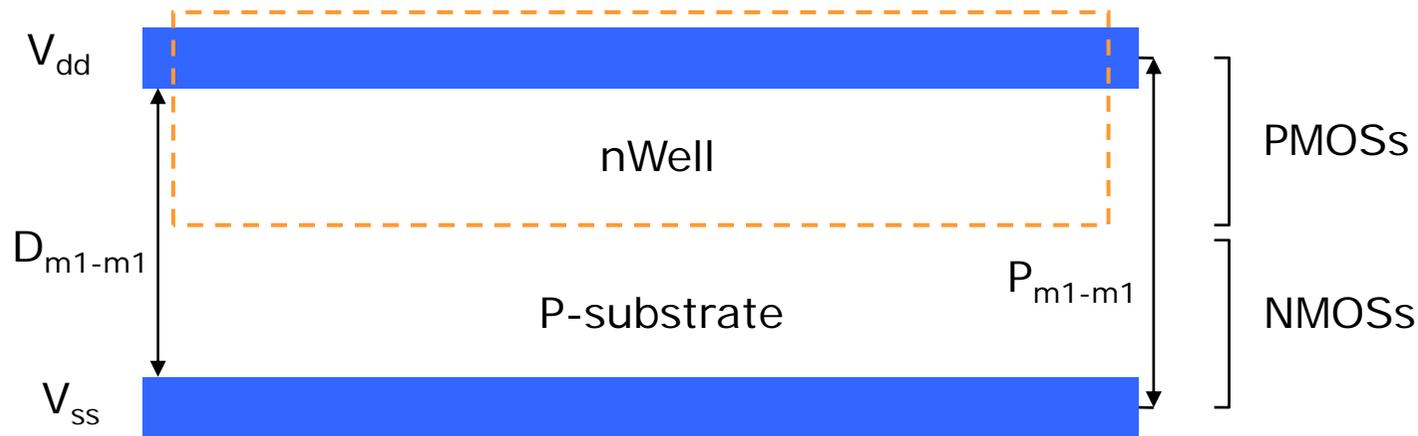
Cell Creation Using Primitive Cells

- Create a new cell providing the function
 - $f = a'b$



Layout of Cells

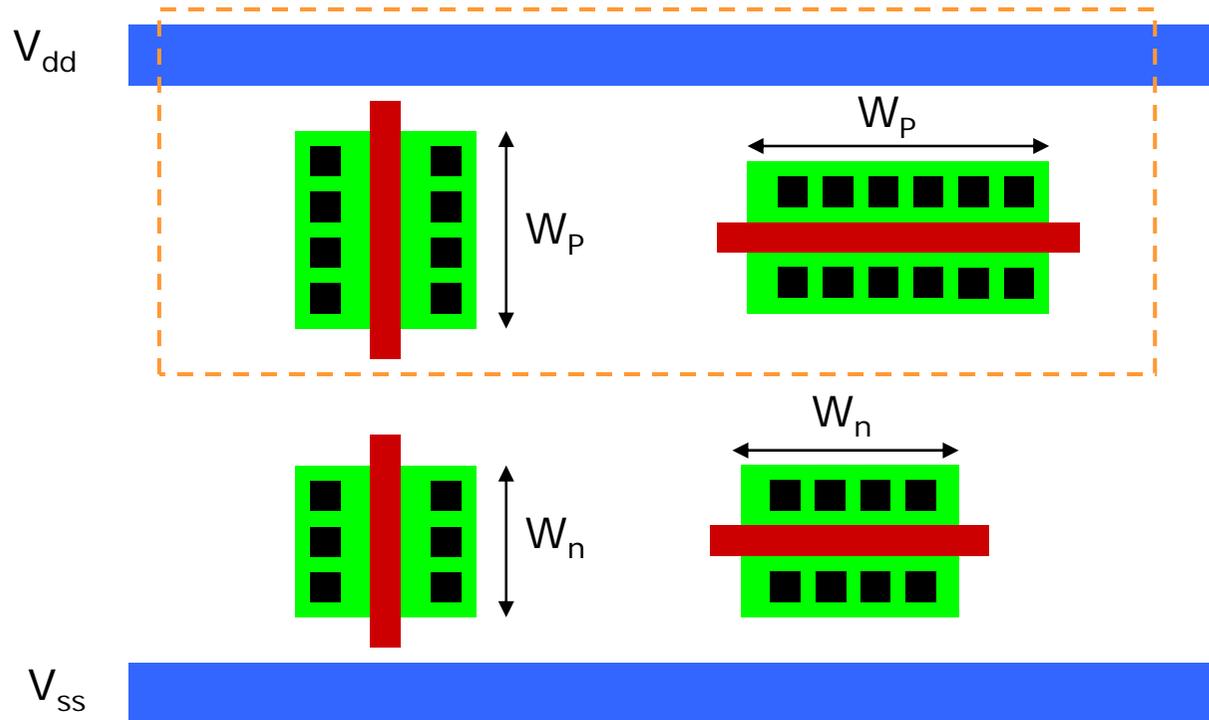
- V_{dd} & V_{ss} power supply lines



- D_{m1-m1} : edge-to-edge distance between V_{dd} and V_{ss}
- P_{m1-m1} : distance between the middle of the V_{dd} and V_{ss} lines
- $P_{m1-m1} = D_{m1-m1} + W_{dd}$, where W_{dd} is the width of the power supply lines

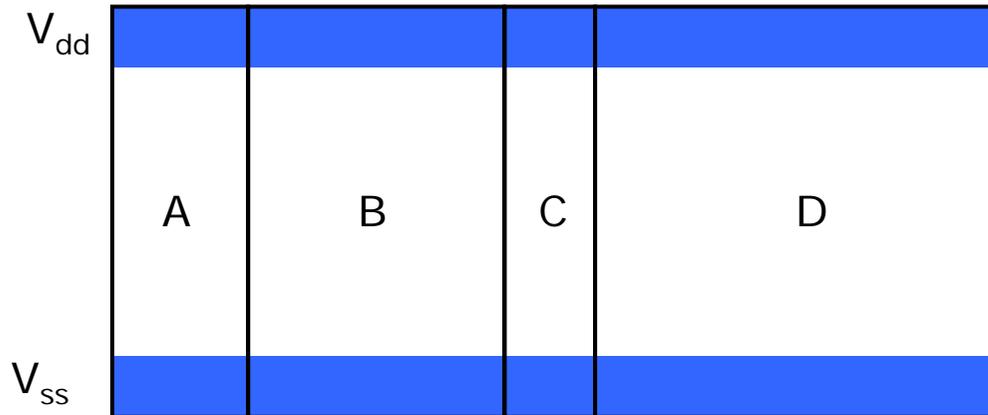
Layout of Cells

□ Layout styles of transistors

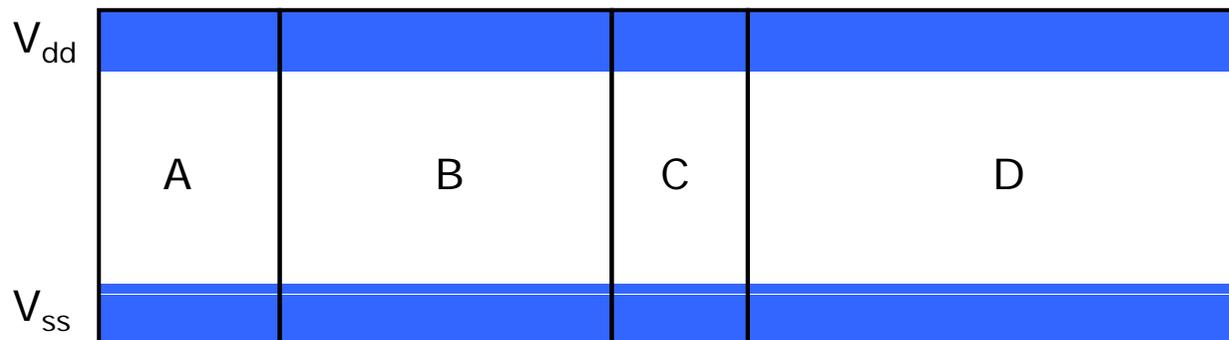


Effect of Layout Shapes

- Larger spacing between V_{dd} and V_{ss}

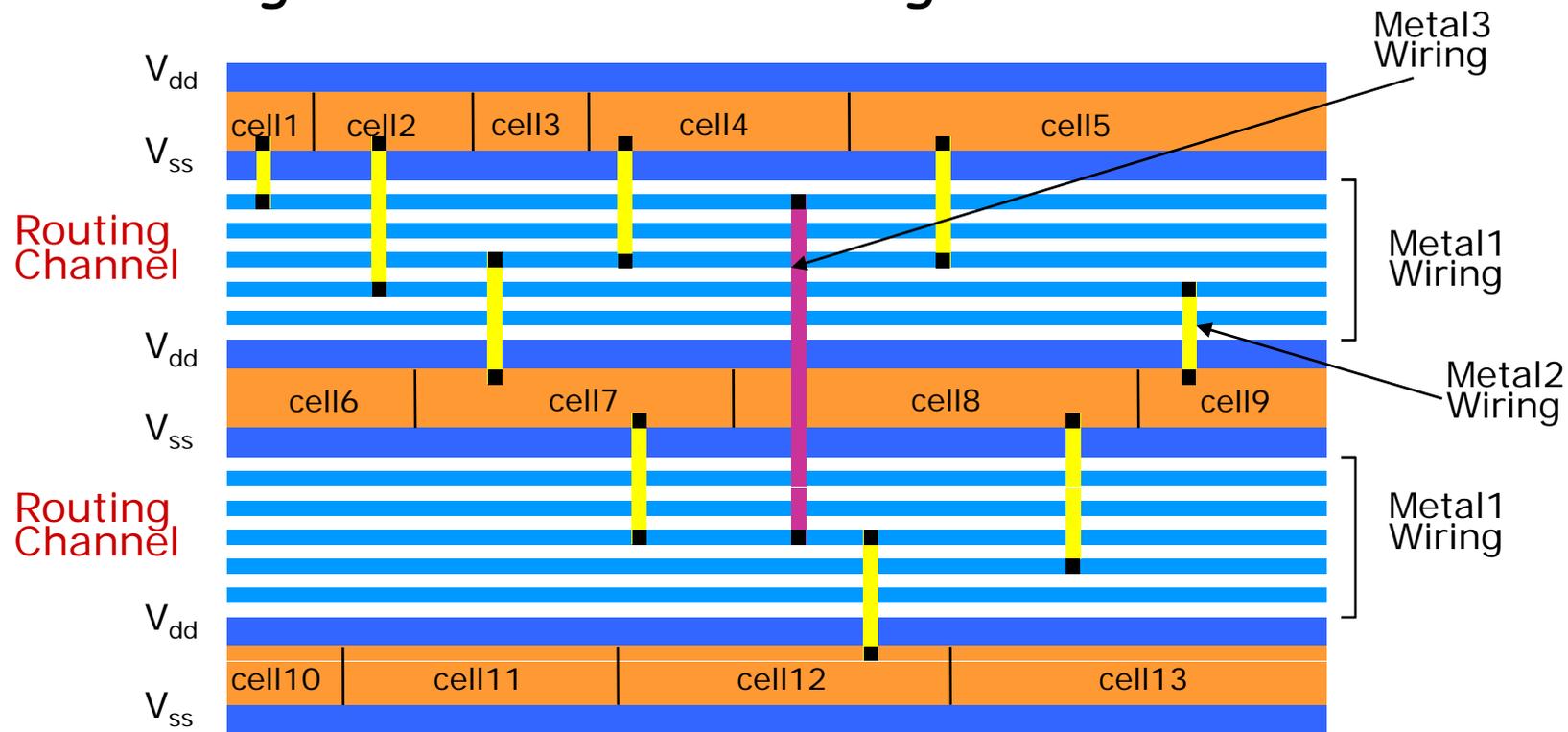


- Smaller spacing between V_{dd} and V_{ss}



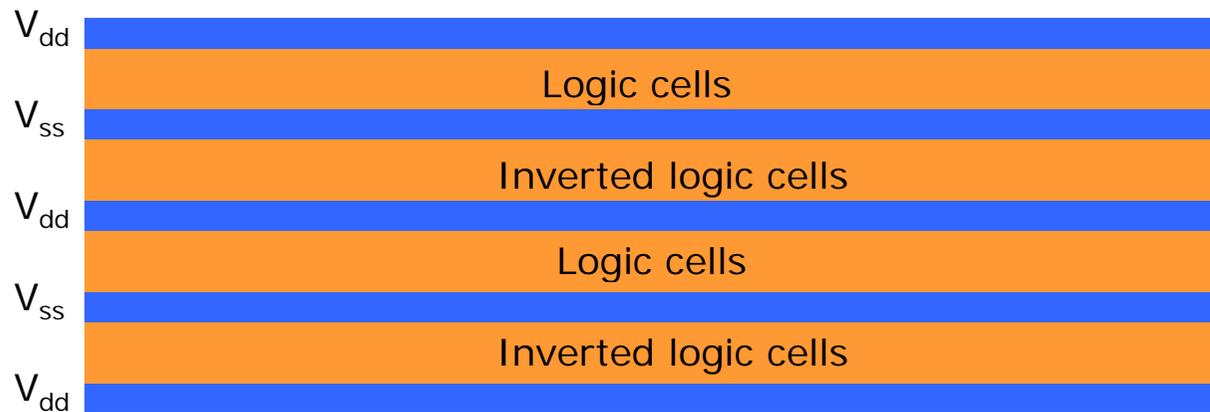
Routing Channels

- Interconnection routing considerations are very important considerations for the $V_{ss}-V_{dd}$ spacing
 - In complex digital systems, the wiring is often more complicated than designing the transistor arrays
 - The general idea for routing



High-Density Techniques

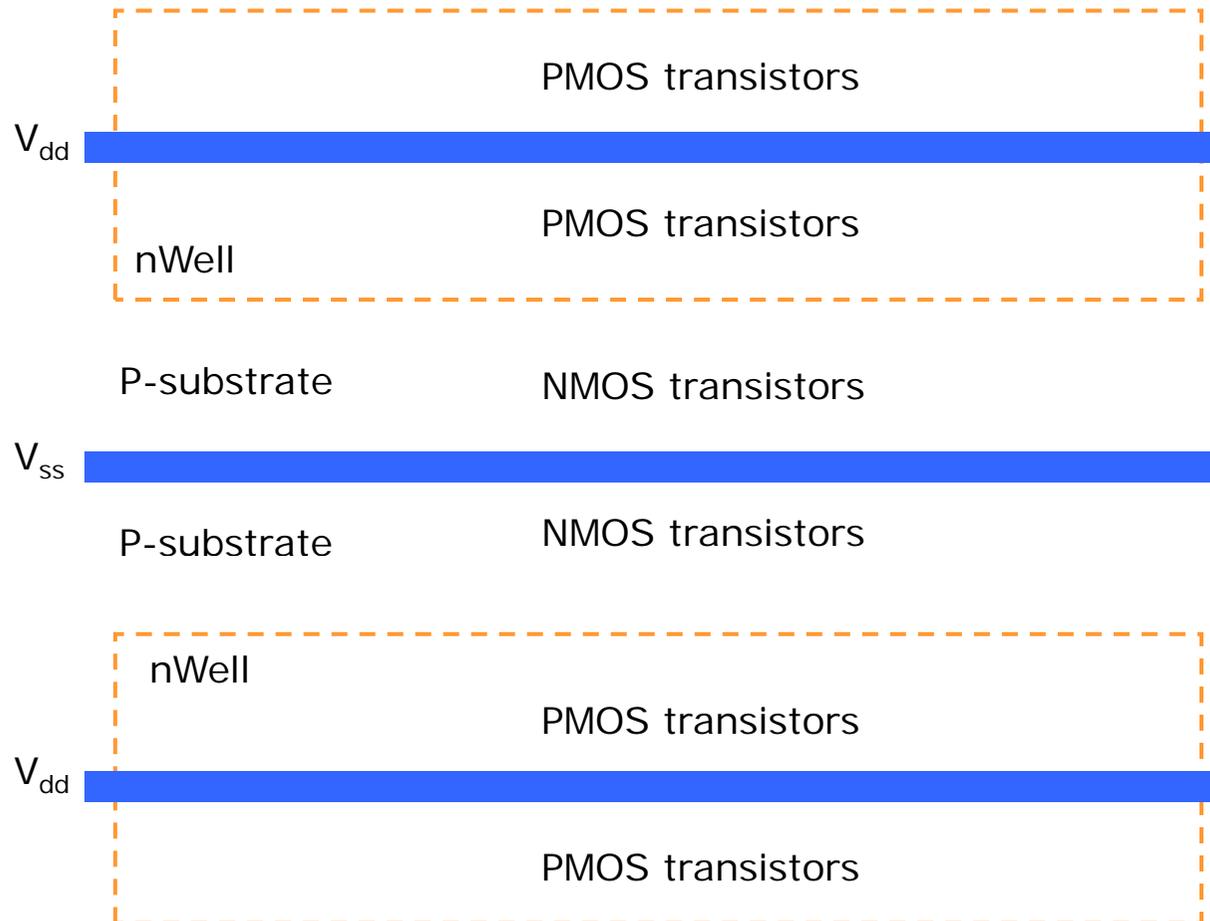
- Alternate V_{dd} and V_{ss} power lines and share them with cells above and below
 - For example,



- Since no space is automatically reserved for routing, this scheme allows for high-density of placement of cells
- The main drawback is that the connection between rows must be accomplished by using Metal2 or higher

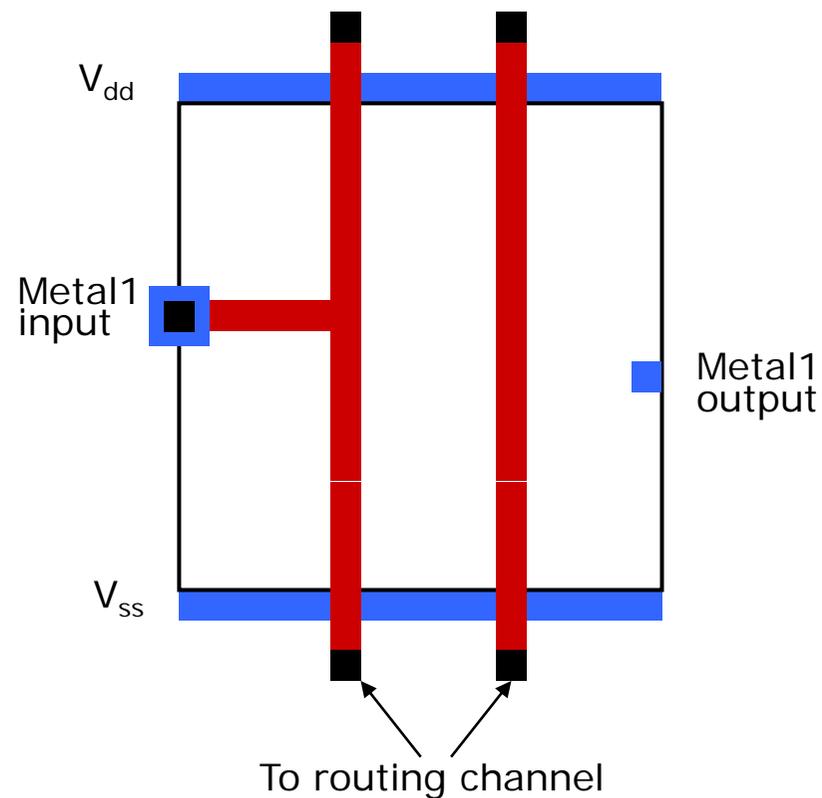
High-Density Techniques

□ MOS transistor placement



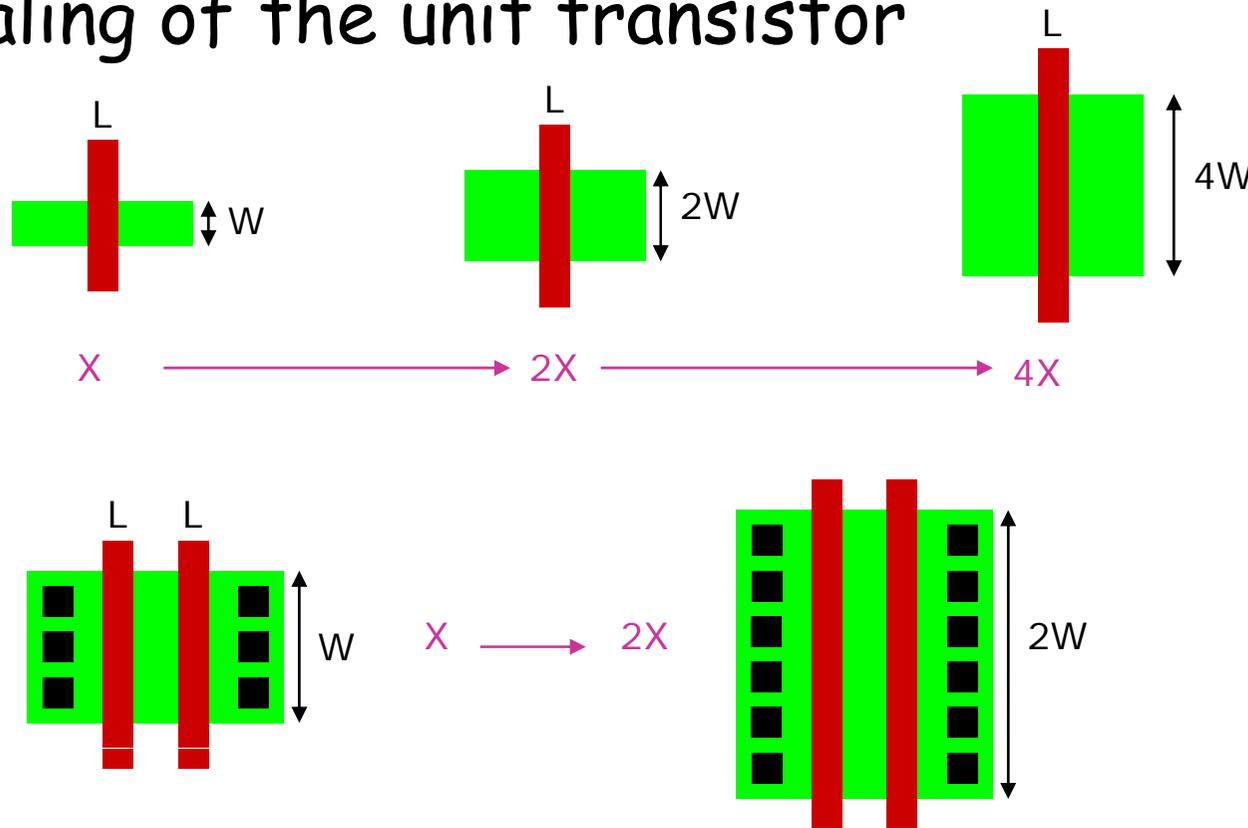
Port Placement

- An example of the port placement in a cell

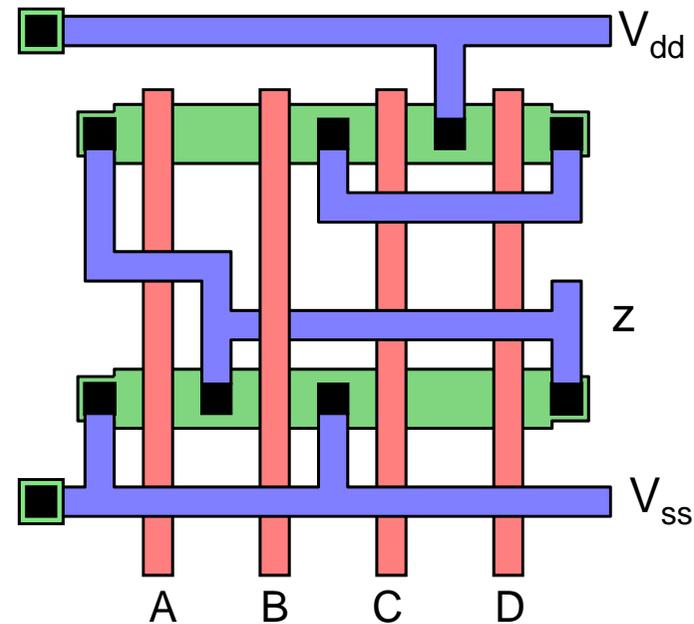
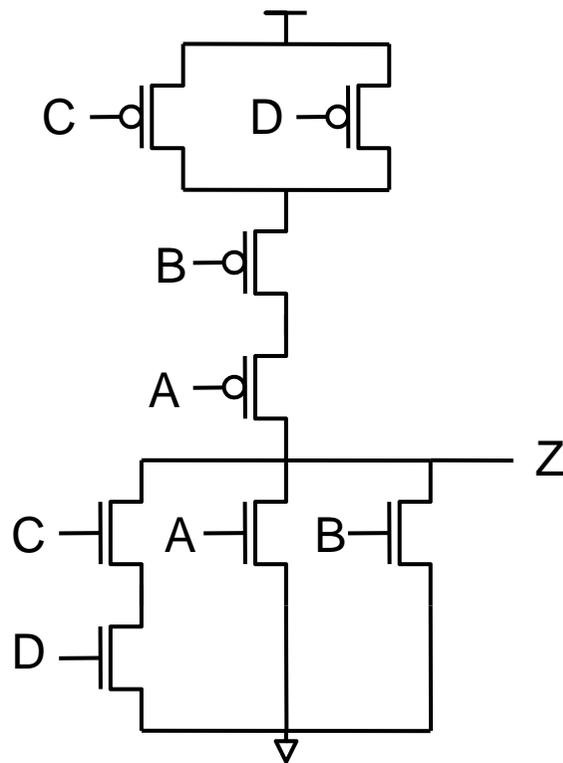


MOS Sizing in Physical Design

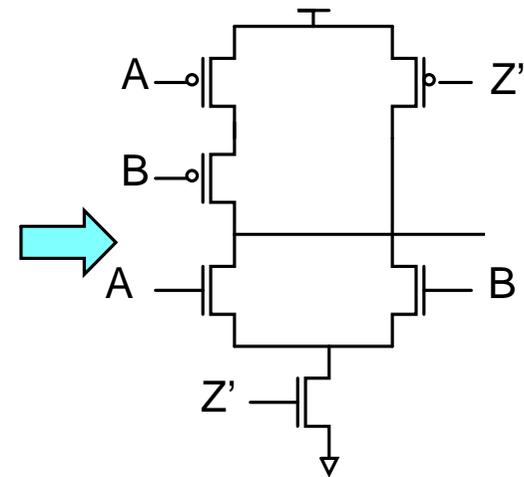
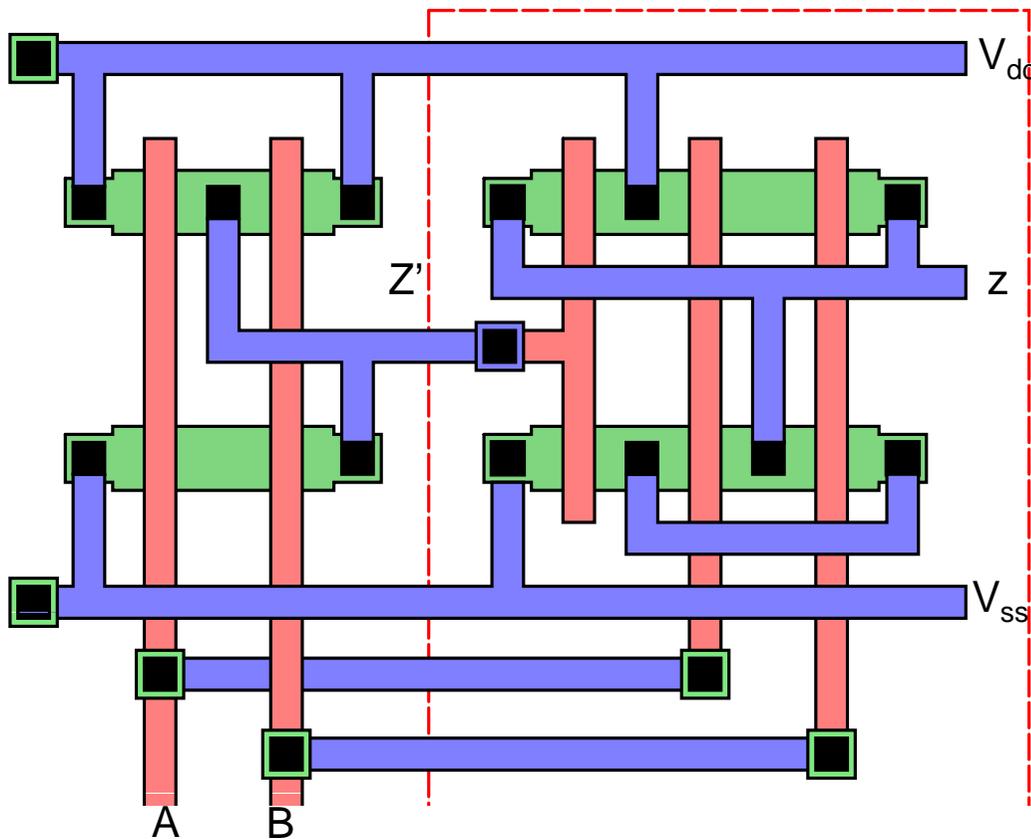
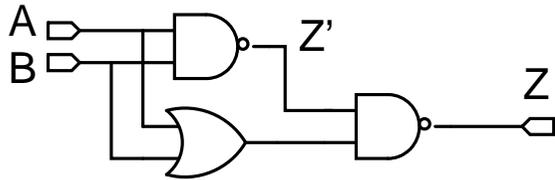
- A minimum-size MOS transistor is the smallest transistor that can be created using the design rule set
- Scaling of the unit transistor



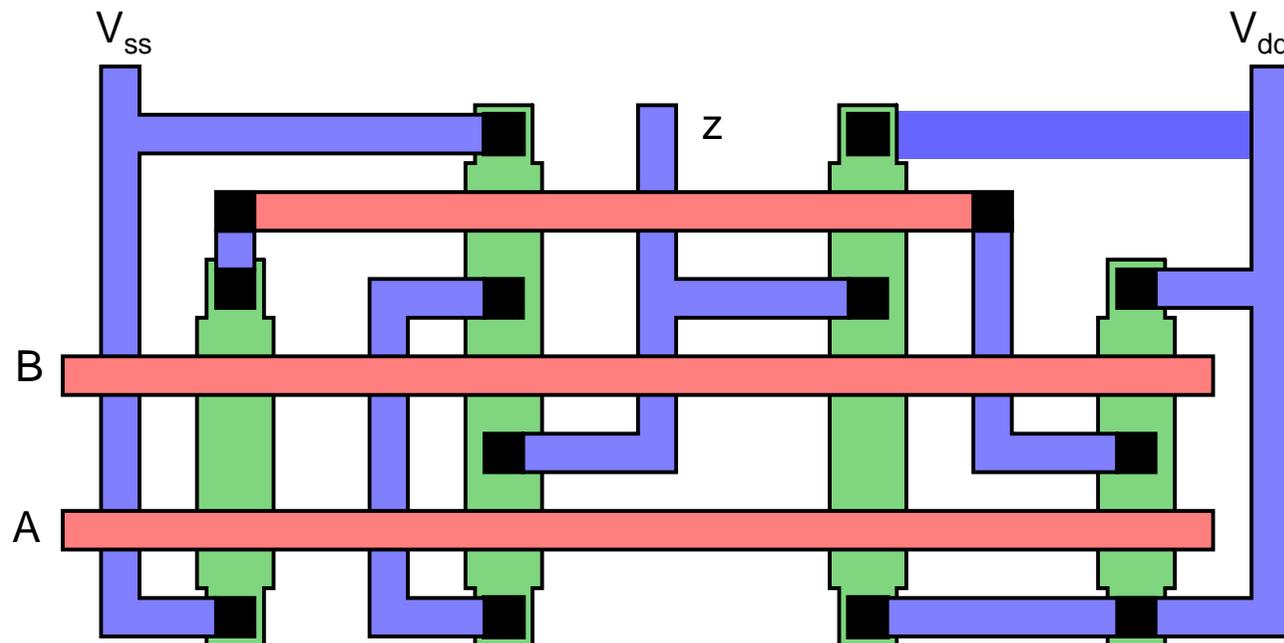
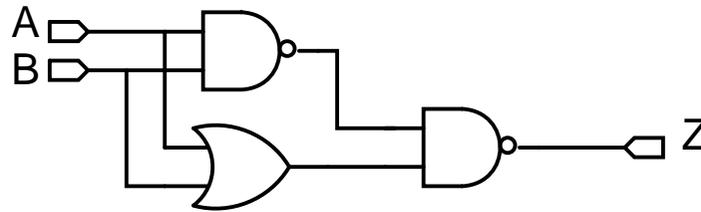
Physical Designs of Complex Gates



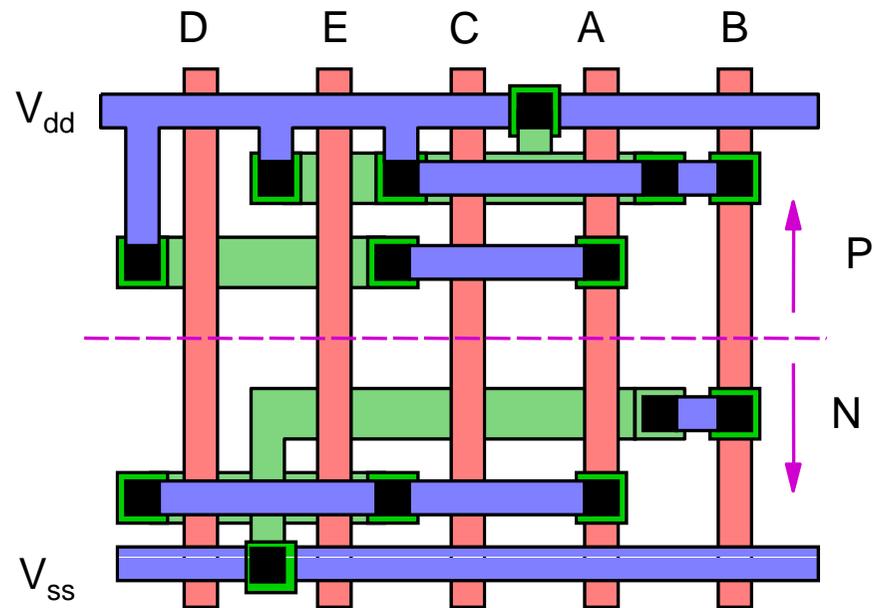
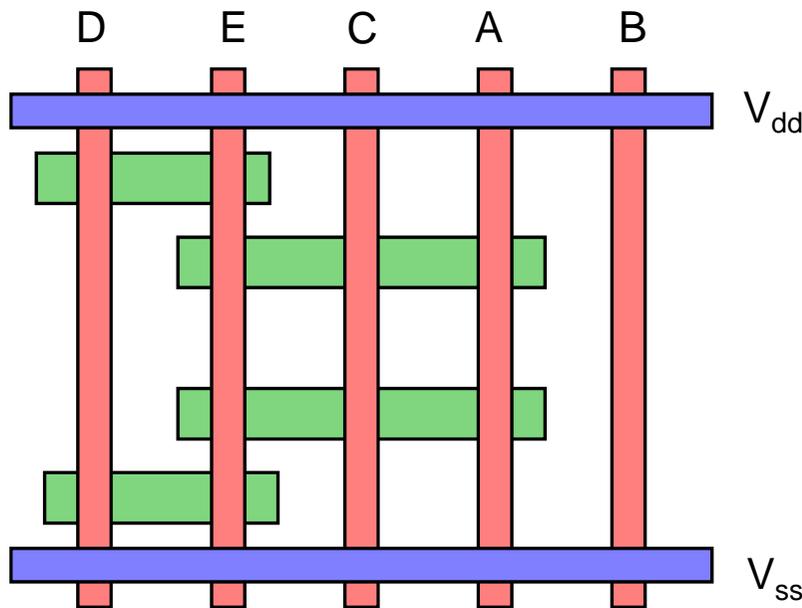
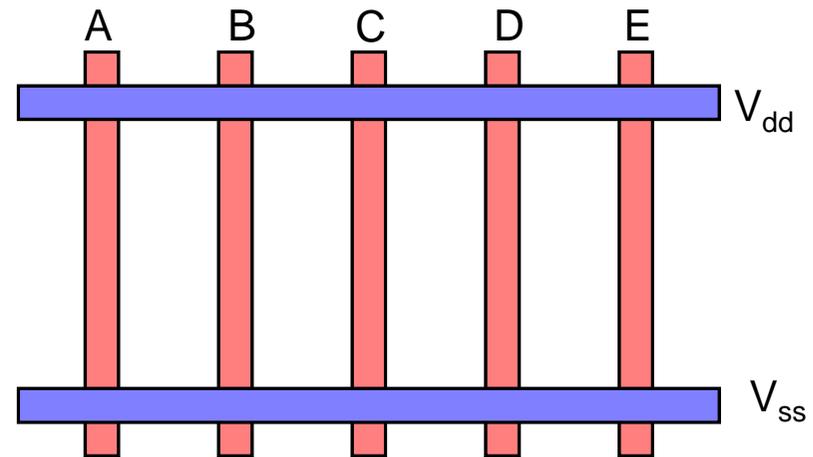
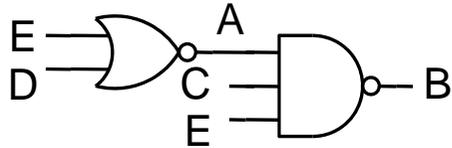
Physical Design of XNOR Gate (1)



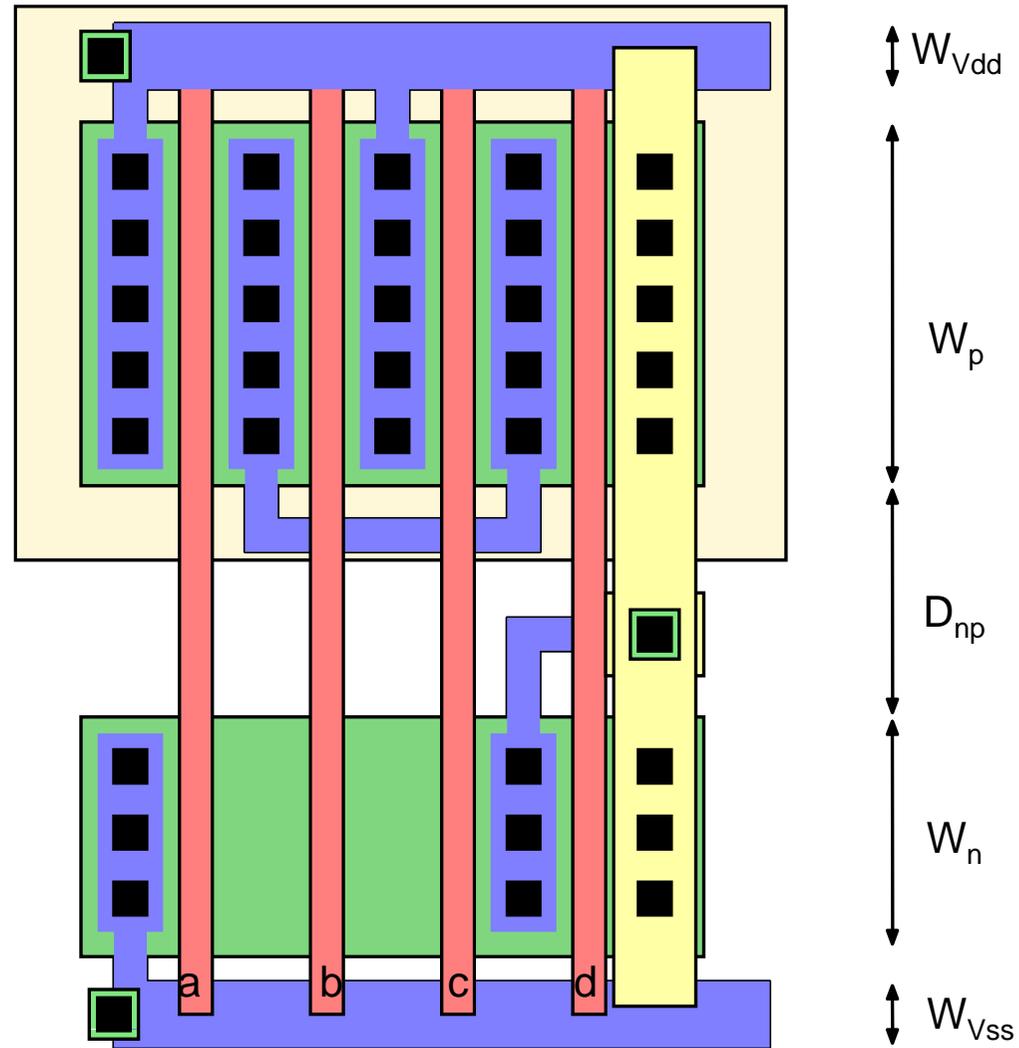
Physical Design of XNOR Gate (2)



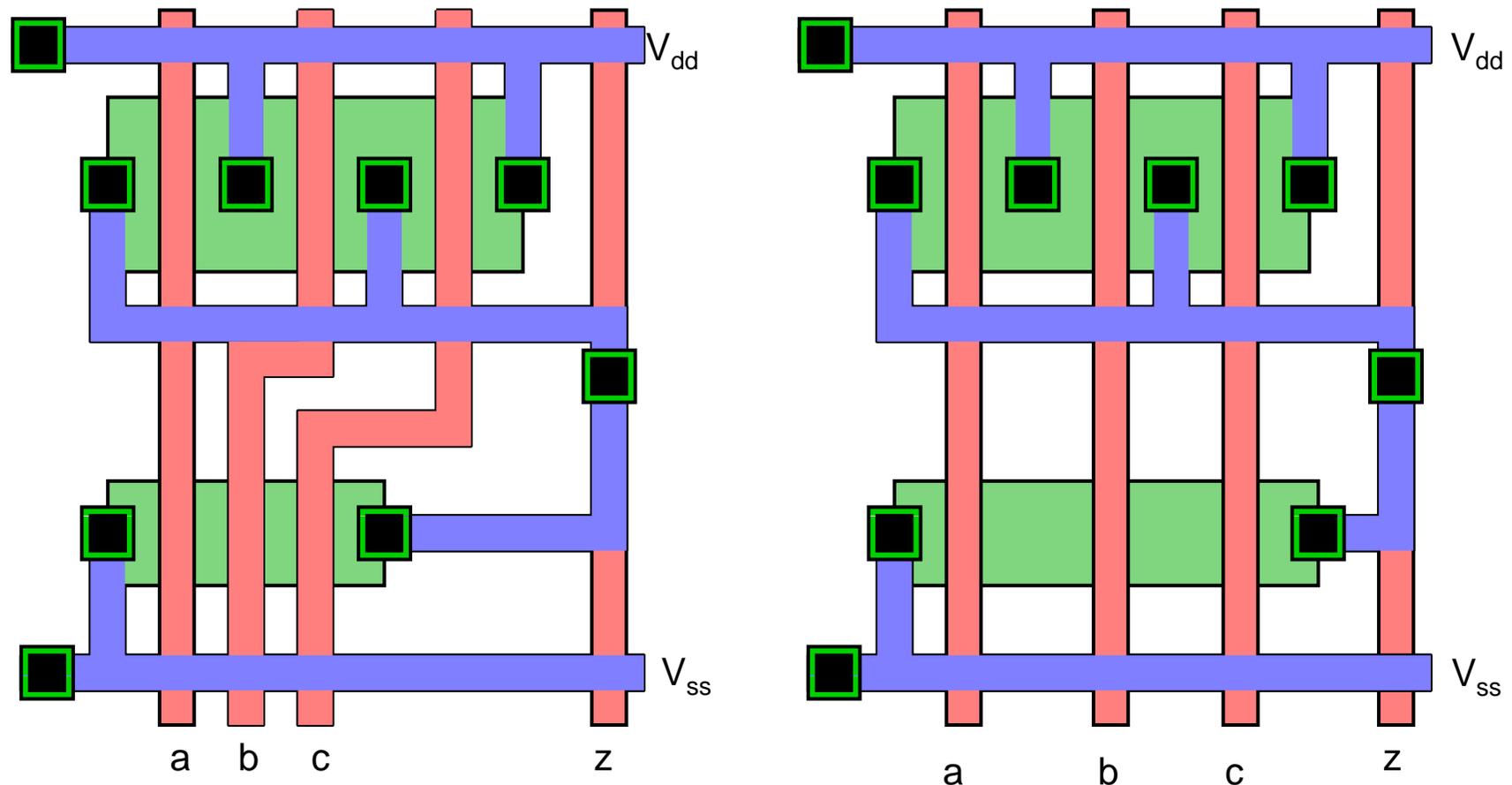
Automation of Physical Design



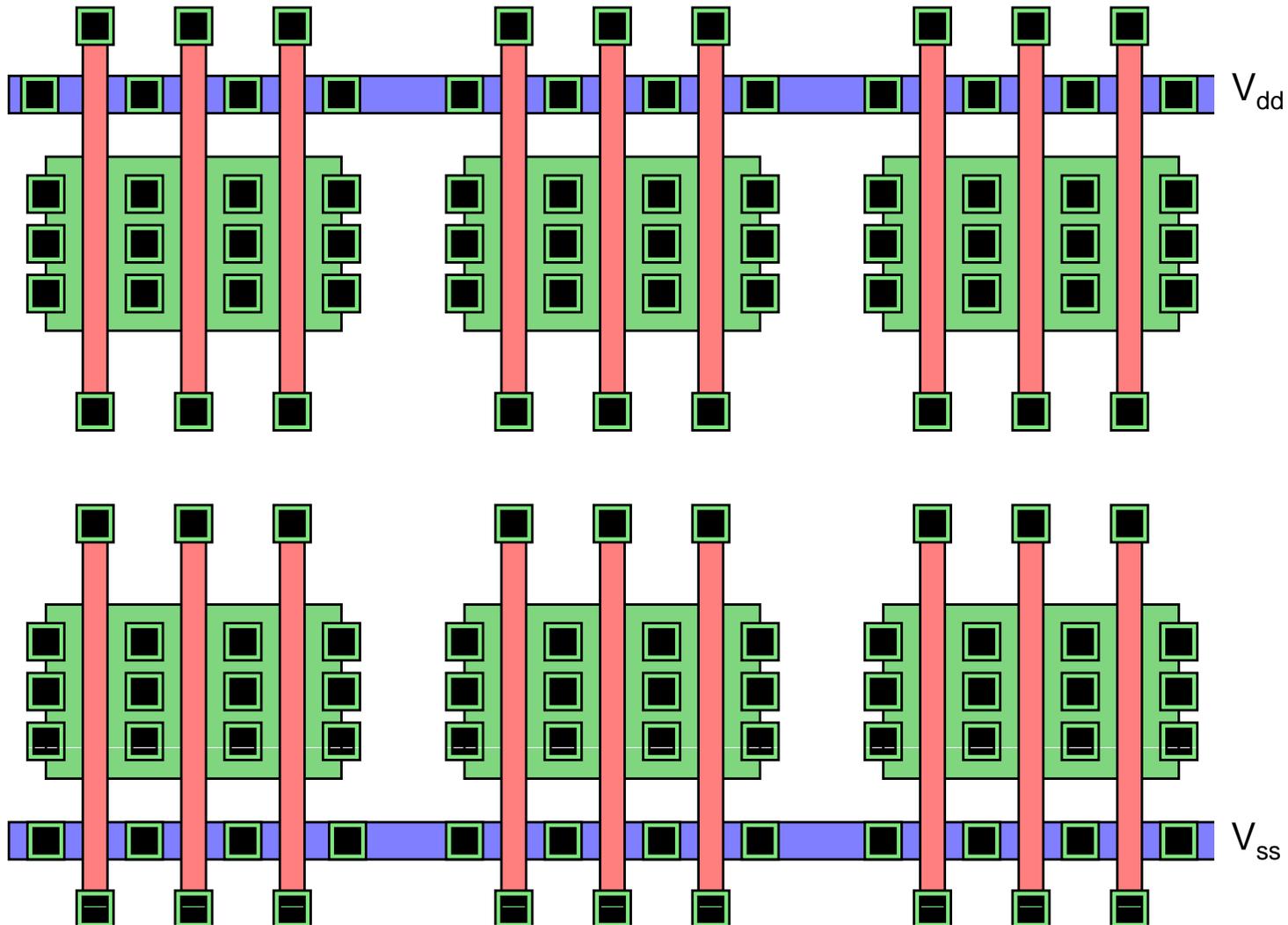
Standard-Cell Physical Design



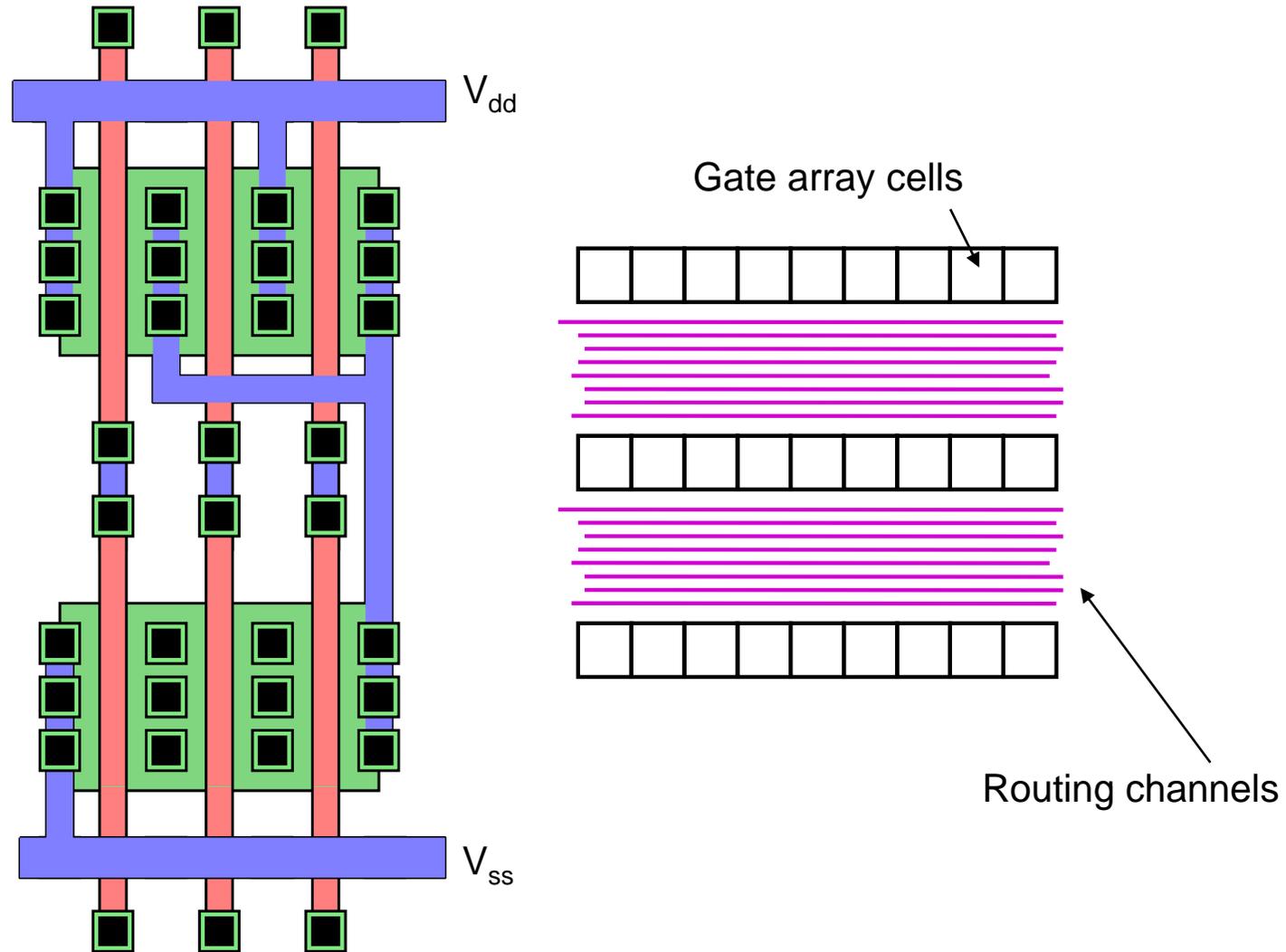
Standard-Cell Physical Design



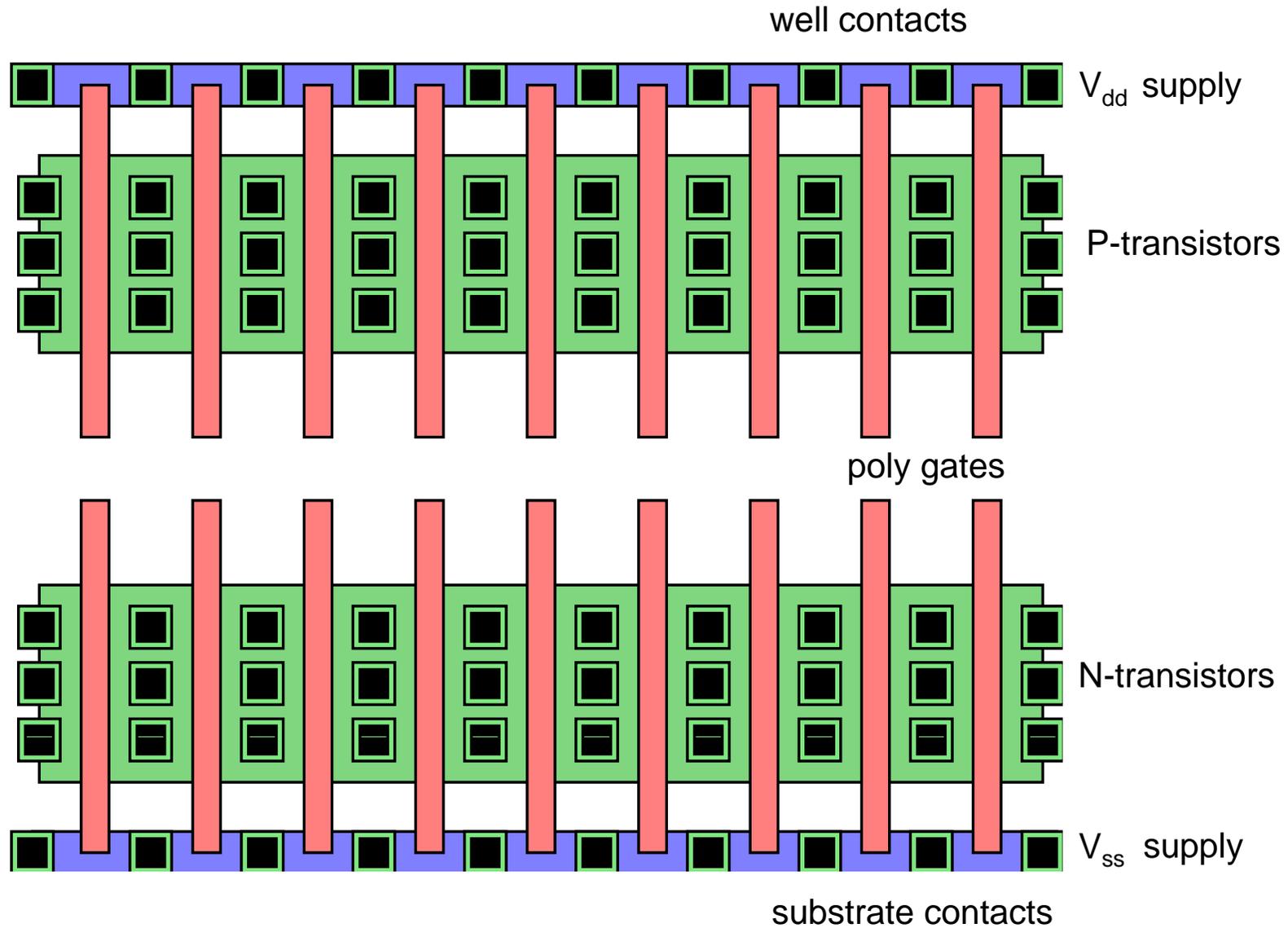
Gate-Array Physical Design



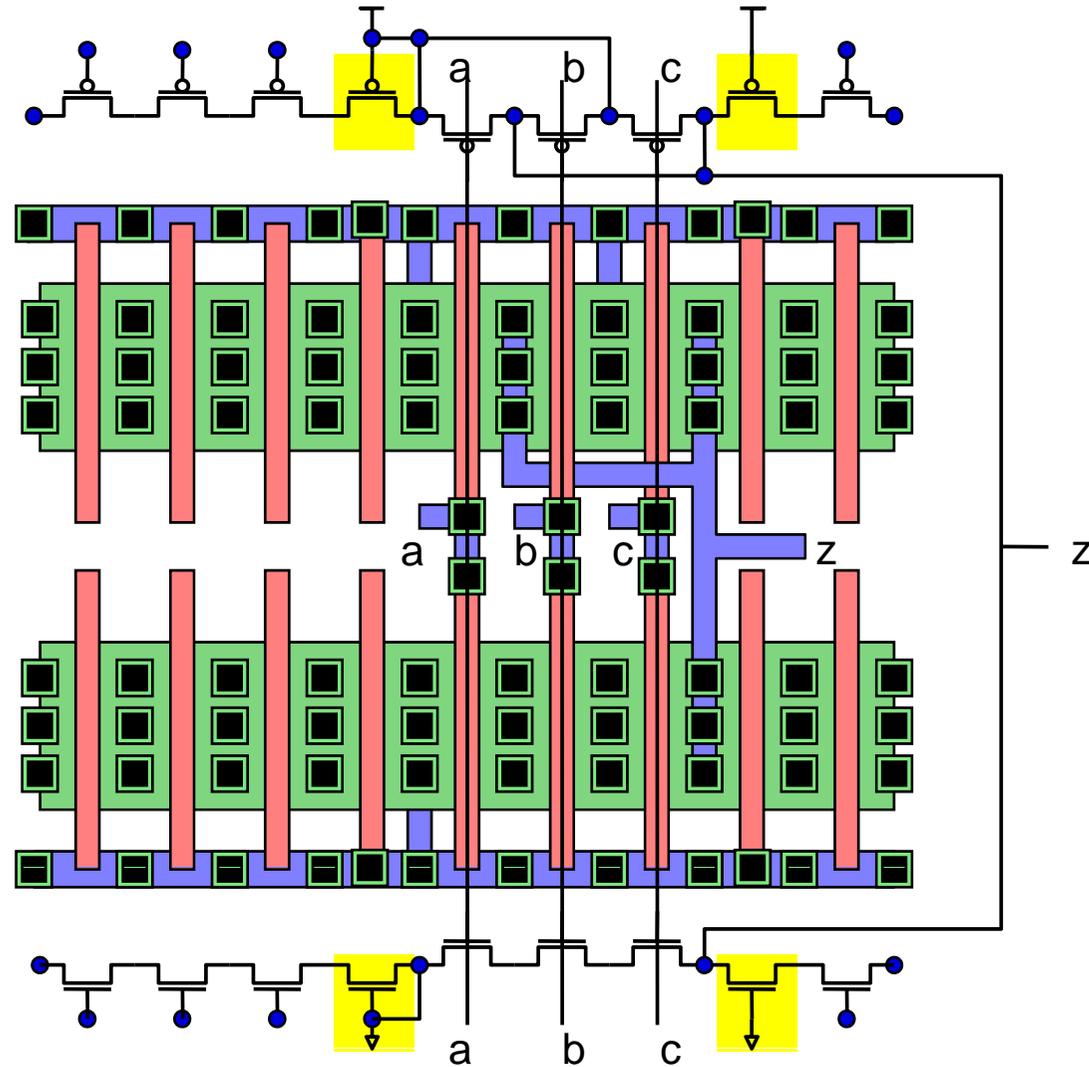
Gate-Array Physical Design



Sea-of-Gate Physical Design



Sea-of-Gate Physical Design



CMOS Layout Guidelines

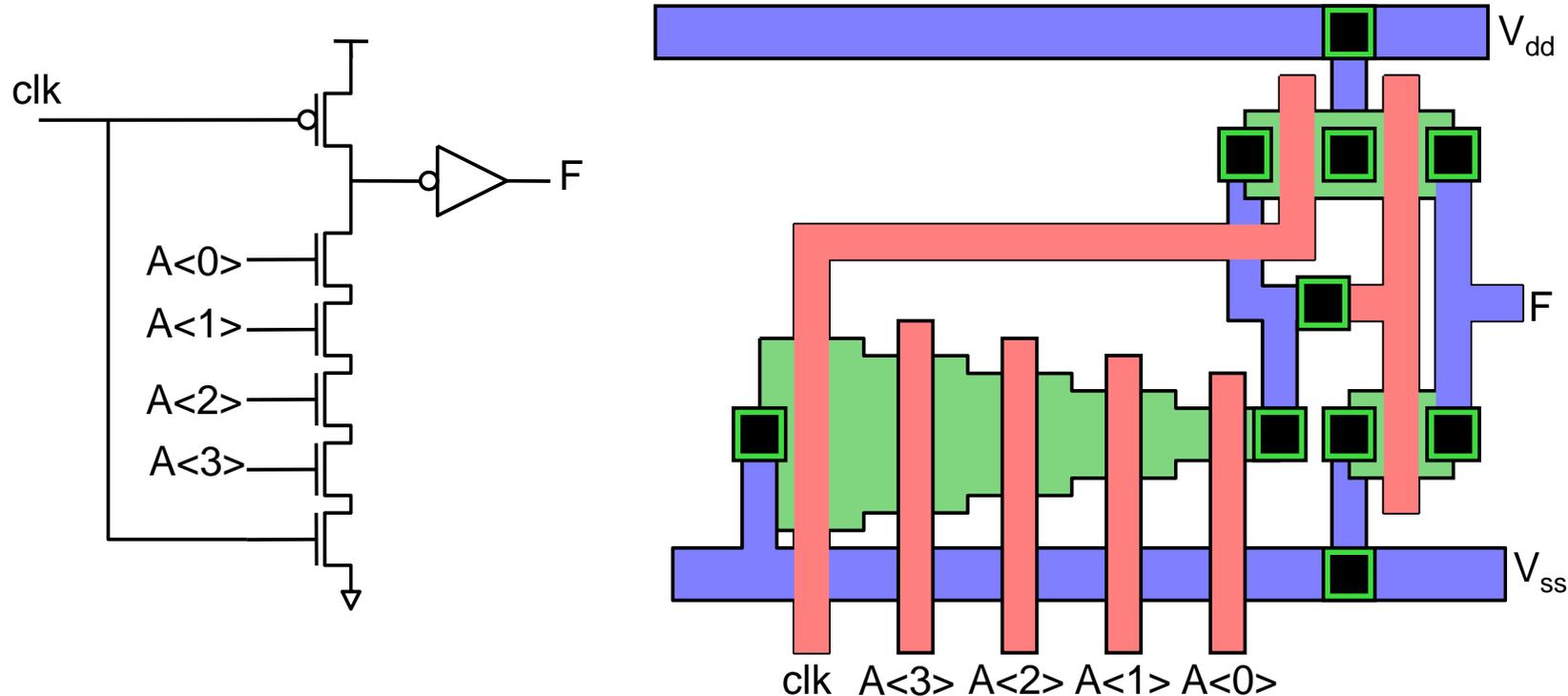
- Run V_{DD} and V_{SS} in metal at the top and bottom of the cell
- Run a vertical poly line for each gate input
- Order the poly gate signals to allow the maximal connection between transistors via abutting source-drain connection
- Place n-gate segments close to V_{SS} and p-gate segments close to V_{DD}
- Connection to complete the logic gate should be made in poly, metal, or, where appropriate, in diffusion

Guidelines for Improving Density

- Better use of routing layers - routes can occur over cells
- More “merged” source-drain connections
- More usage of “white” space in sparse gates
- Use of optimum device sizes - the use of smaller devices leads to smaller layouts

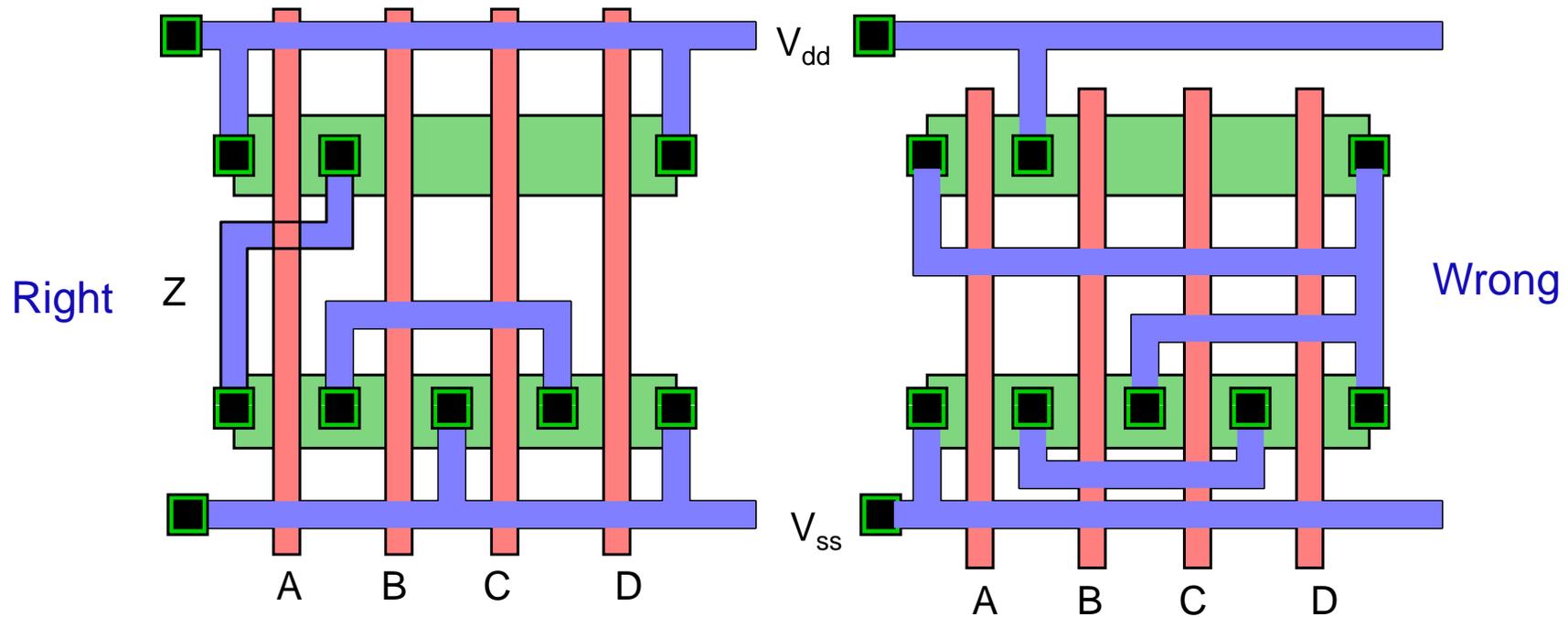
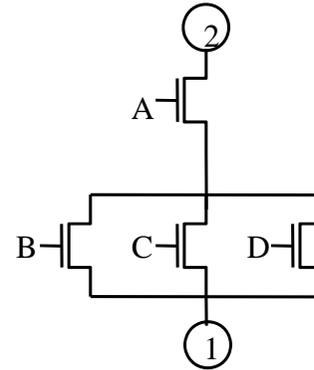
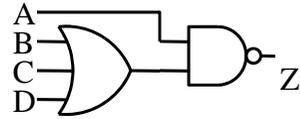
Layout Optimization

- Vary the size of the transistor according to the position in the structure

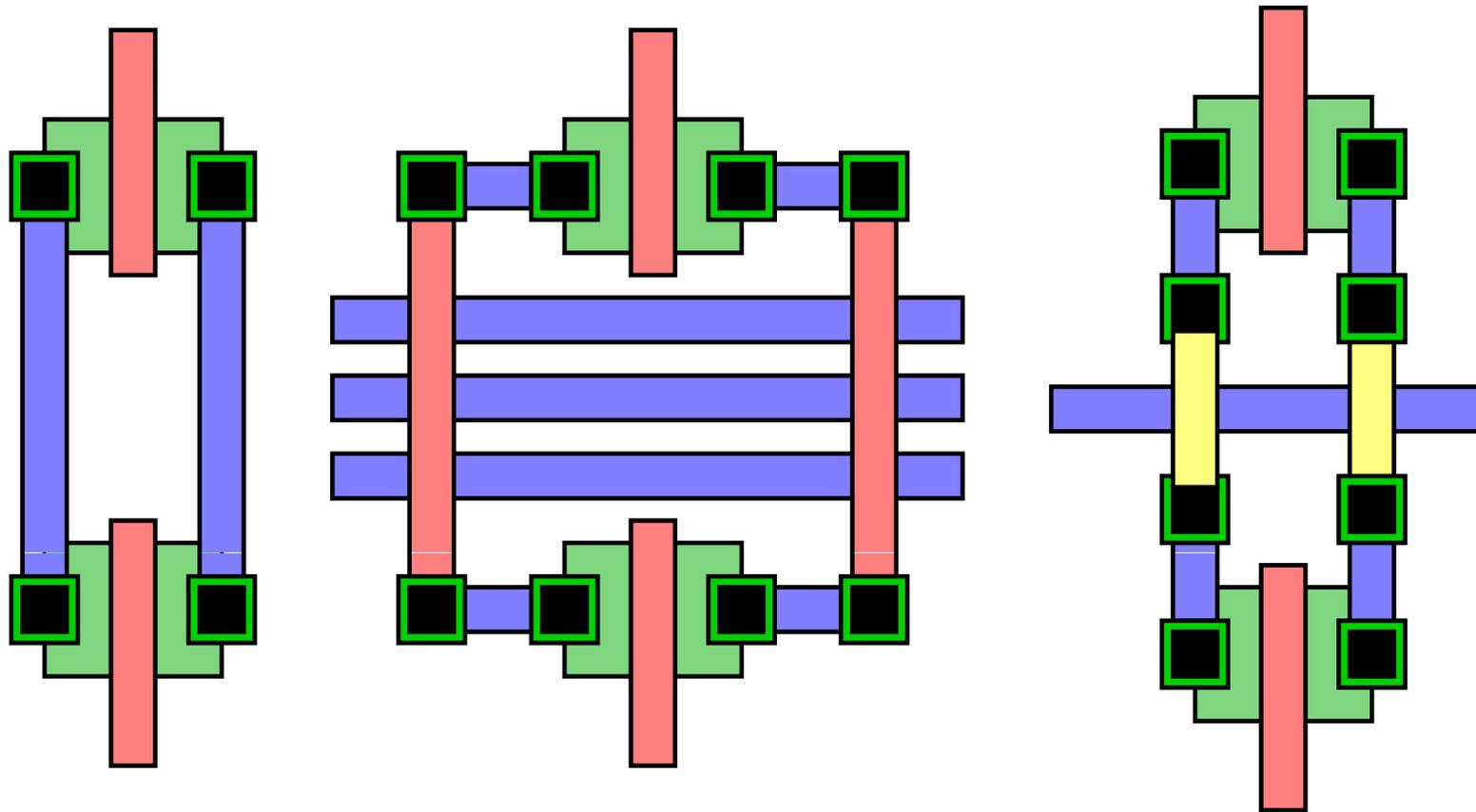


- In submicron technologies, where the source/drain capacitances are less, such that this improvement is limited

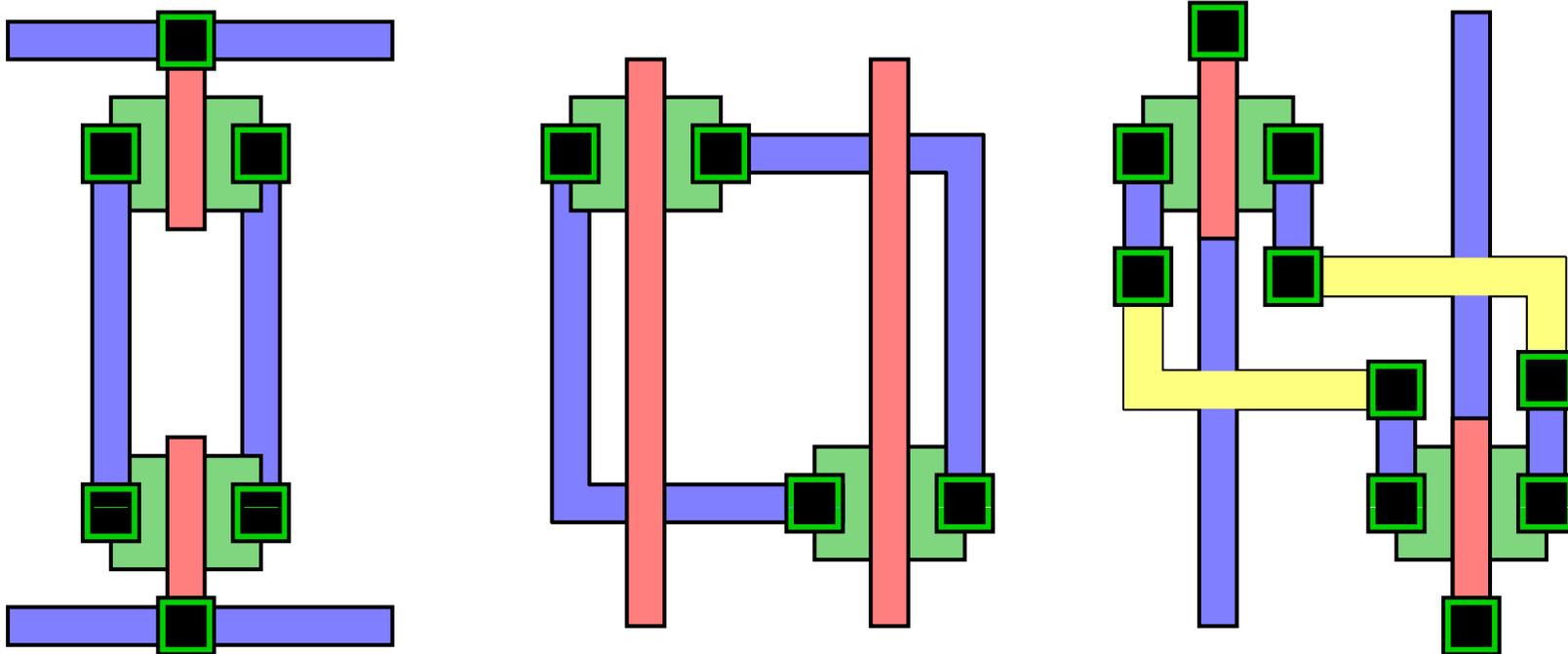
Layout Optimization



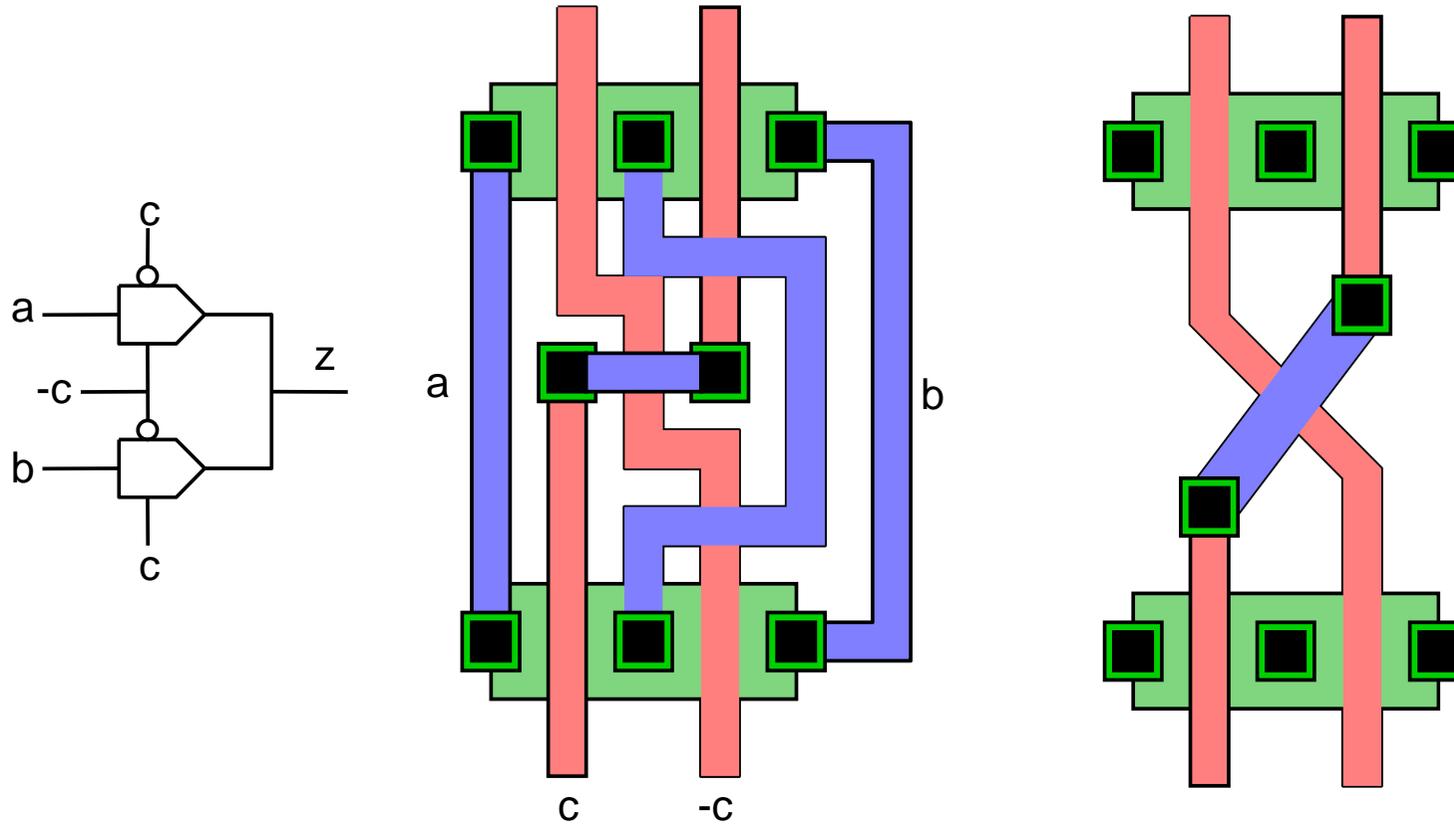
Layouts of Transmission Gates



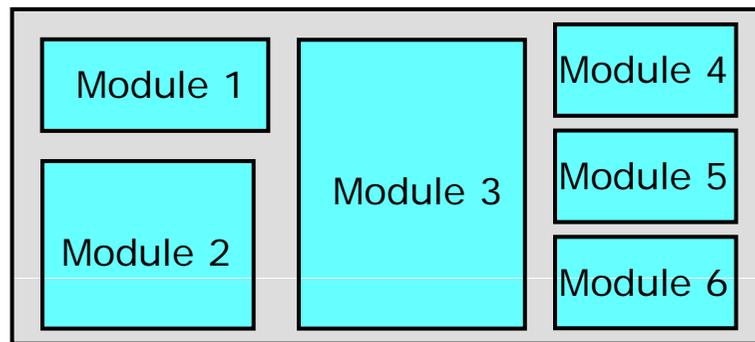
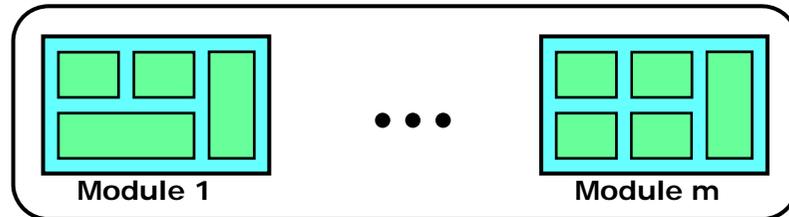
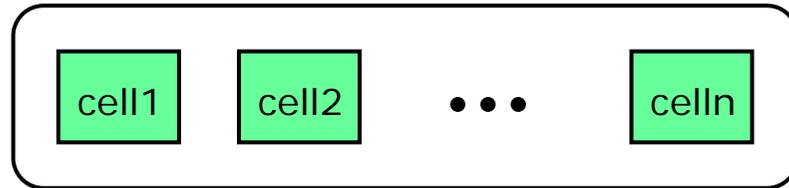
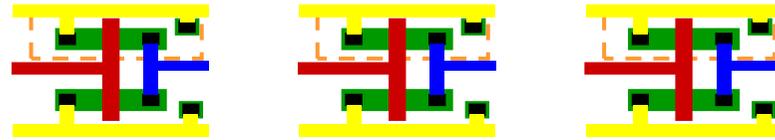
Routing to Transmission Gates



2-Input Multiplexer



Design Hierarchies



Layout level



Cell library



Subsystems



Chips

Summary

- Basic physical design concepts have been introduced
- Cell concepts have also presented
- Layout optimization guidelines have been summarized
- Design hierarchy has been briefly introduced